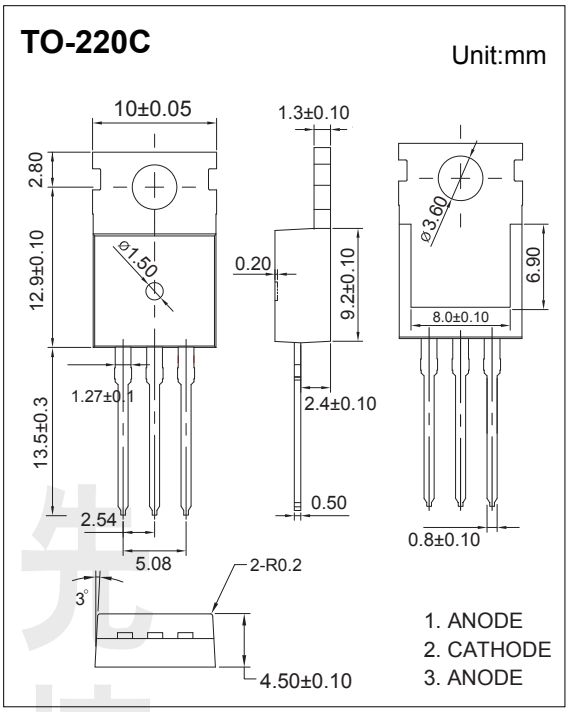
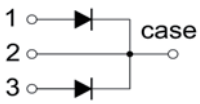
Schottky Barrier Rectifier

MBR20100CT



■ Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss,High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters,Free Wheeling, and Polarity Protection Applications



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	100	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS reverse voltage	$V_{R(RMS)}$	70	
Average rectified output current @Tc=125℃	I_O	20	A
Non-Repetitive peak forward surge current @ 8.3ms	I_{FSM}	120	
Power dissipation	P_D	2	W
Thermal resistance junction to ambient	$R_{\theta JA}$	50	℃/W
Junction temperature	T_J	150	℃
Storage temperature	T_{STG}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R=1mA	100			V
Reverse voltage leakage current	I_R	V_R=100V			0.1	mA
Forward voltage	V_F	I_F=10A			1	V
		I_F=20A			1.2	

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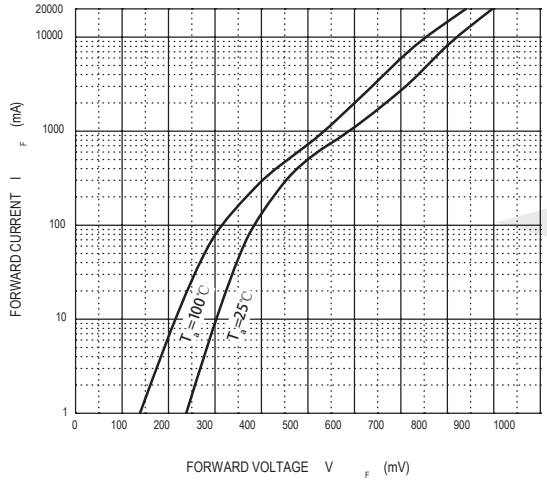
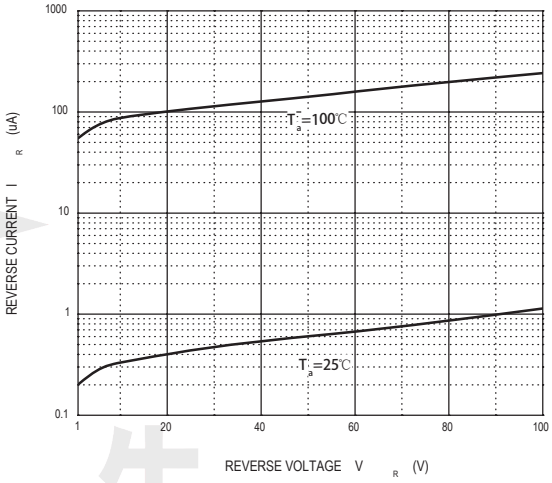
■ Typical Characteristics

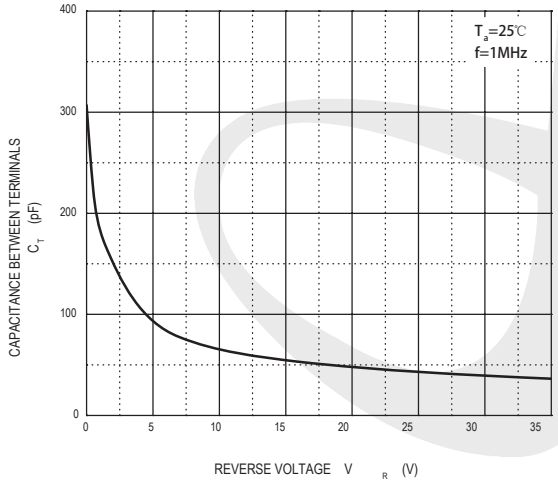
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



I_O vs T_C